

**NEW
PRODUCTS**

3.3V/5V Stepping Down DC to DC Converter Power IC **MD1320N**



1.5A PWM Control Stepping Down Converter IC
It achieves High Output Power and High Efficiency
integrating high performance and high function in compact
package

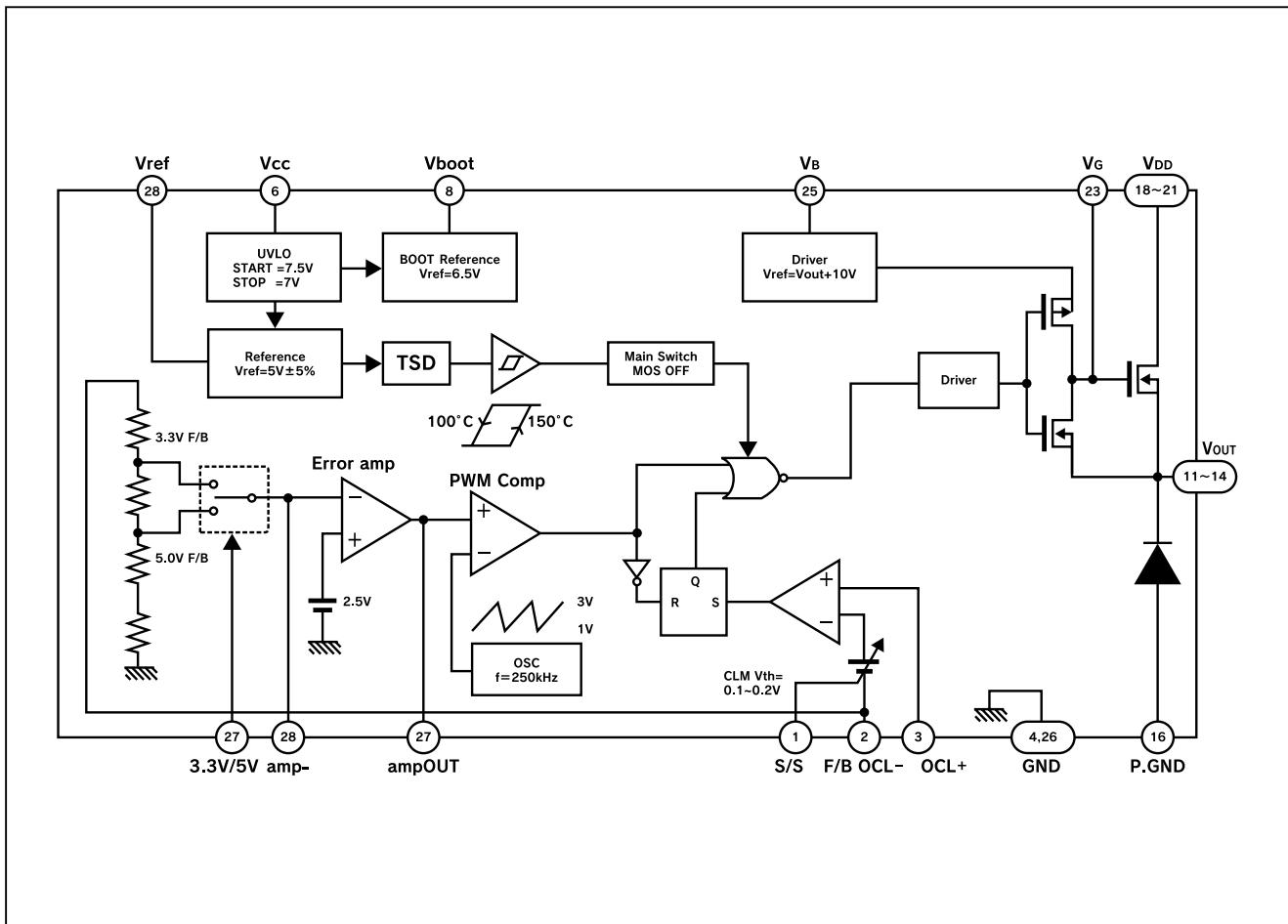
■ Summary

MD1320N is a non-isolated, PWM control stepping down DC to DC converter power IC including main MOSFET switch and fly wheel SBD inside. It has maximum 7.5W(5V, 1.5A) output power and high efficiency in wide range. It also has wide input voltage rangee (8 - 30V) and it is possible to get 3.3V or 5V output voltage by selecting terminal. Its package is new compact surface mount type (SSOP-32) and it is possible to design DC to DC converter with fewer external components and smaller mounting area.

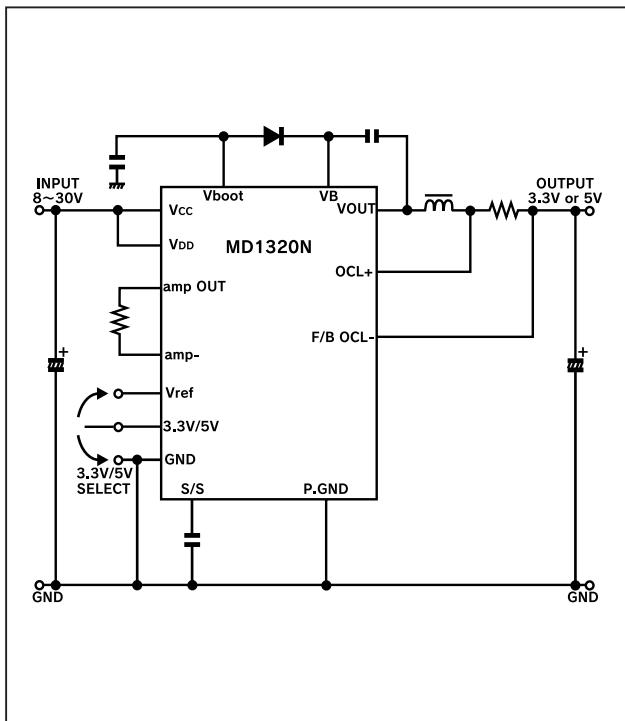
■ Feature

- Input Voltage range 8-30V
- Maximum Output Current 1.5A
- Included main MOSFET switch and fly wheel SBD
- Output 3.3V / 5V (Selective with output switching terminal)
- High Efficiency typ. 91% (at:Vin=8V, Vout=5V, Iout=0.5A)
- Fixed Frequency 250kHz PWM Control
- Over Current Protection Function
- Low Input Voltage Protection Function(UVLO)
- Thermal Shut Down Function

■ Block Diagram



■ Application Example



■ Pin Layout

S/S : 1	32 : amp-
F/B OCL- : 2	31 : N/C
OCL+ : 3	30 : ampOUT
GND : 4	29 : N/C
N/C : 5	28 : Vref
Vcc : 6	27 : 3.3V/5V
N/C : 7	26 : GND
Vboot : 8	25 : Vb
N/C : 9	24 : N/C
N/C : 10	23 : VG
Vout : 11	22 : N/C
Vout : 12	21 : Vdd
Vout : 13	20 : Vdd
Vout : 14	19 : Vdd
N/C : 15	18 : Vdd
P.GND : 16	17 : N/C

■ Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Line voltage	VIN	32	V
Output MOS input voltage	VDD	32	V
Output current (AVE)	IOUTave	1.5	A
Output current (PEAK)	IOUTpeak	2	A
Storage temperature	Tstg	-40~150	°C
Junction temperature	Tj	150	°C

■ Recommended Operation Conditions

Item	Recommended Value	Unit
Input voltage	8~30	V
Operation temperature	-10~80	°C

■ Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	MIN	TYP	MAX	Unit
HighsideMOS Drain-source breakdown voltage	Vdss	ID=1mA, VGS=0V	32	—	—	V
HighsideMOS Drain interruption current	Idss	VDS=30V, VGS=0V	—	—	10	μA
HighsideMOS Drain-source ON resistance	Ron	ID=1.2A, VGS=4V	—	140	250	mΩ
HighsideMOS Source-drain Di forward voltage	VSD	Is=1.2A, VDS=0V	—	—	1.5	V
LowSideSBD Peak reverse voltage	VRM	—	40	—	—	V
LowSideSBD Forward voltage	VF	IF=1.2A	—	—	0.55	V
LowSideSBD Reverse current	IR	VR=VRM	—	—	2	mA
Start voltage	Vcc_start	—	7	7.5	8	V
Stop voltage	Vcc_stop	—	6.5	7	7.5	V
Start-stop voltage hysteresis	Vcc_hys	—	—	0.5	—	V
Current consumption	Icc	Vcc=8V~30V	—	8	10	mA
BOOT terminal voltage	Vboot	Vcc=8V~30V	6	6.5	7	V
Internal reference voltage	Vref	Vcc=8V~30V	4.75	5	5.25	V
Internal oscillation frequency	fosc	Vcc=24V	212.5	250	287.5	kHz
Overcurrent threshold voltage	Vth_OCL	Vcc=24V	0.162	0.19	0.218	V
SoftStart terminal current	Is/s	Vcc=24V	-20	-12.5	-5	μA
"H" CHG terminal input voltage	VCHGH	—	4.5	—	Vref	V
"L" CHG terminal input voltage	VCHGL	—	GND	—	0.5	V
Overcurrent protection operating temperature	T_TSD	—	—	150	—	°C

